



SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

CPH3351 — P-Channel Silicon MOSFET — General-Purpose Switching Device Applications

Features

- ON-resistance $R_{DS(on)1}=190m\Omega$ (typ.)
- 4V drive
- Halogen free compliance
- Protection diode in

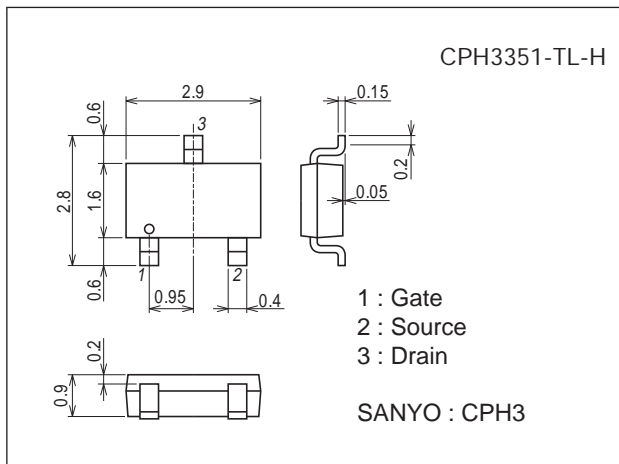
Specifications

Absolute Maximum Ratings at $T_a=25^\circ C$

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		-60	V
Gate-to-Source Voltage	V_{GSS}		± 20	V
Drain Current (DC)	I_D		-1.8	A
Drain Current (Pulse)	I_{DP}	$PW \leq 10\mu s$, duty cycle $\leq 1\%$	-7.2	A
Allowable Power Dissipation	P_D	When mounted on ceramic substrate (900mm ² ×0.8mm)	1	W
Channel Temperature	T_{ch}		150	°C
Storage Temperature	T_{stg}		-55 to +150	°C

Package Dimensions

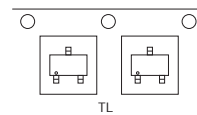
unit : mm (typ)
7015A-004



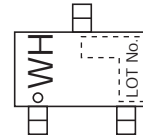
Product & Package Information

- Package : CPH3
- JEITA, JEDEC : SC-59, TO-236, SOT-23
- Minimum Packing Quantity : 3,000 pcs./reel

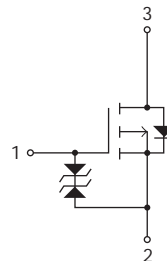
Packing Type: TL



Marking



Electrical Connection

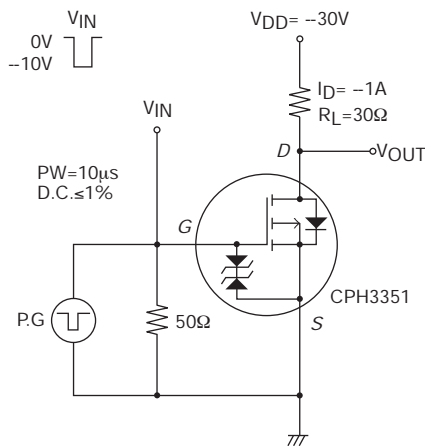


CPH3351

Electrical Characteristics at Ta=25°C

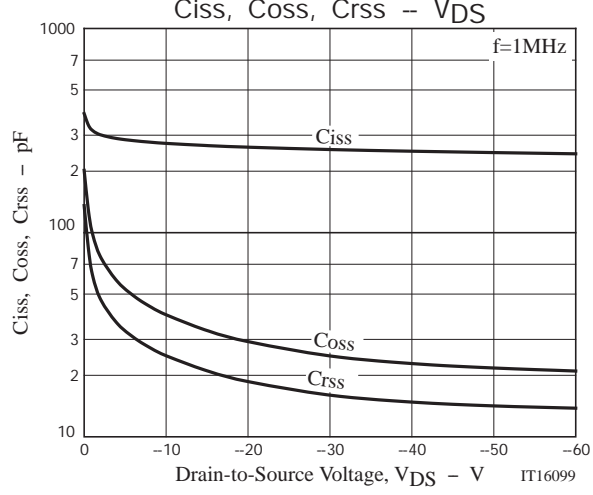
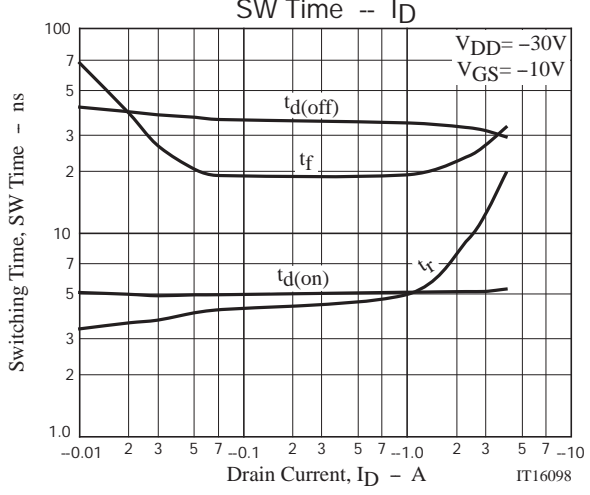
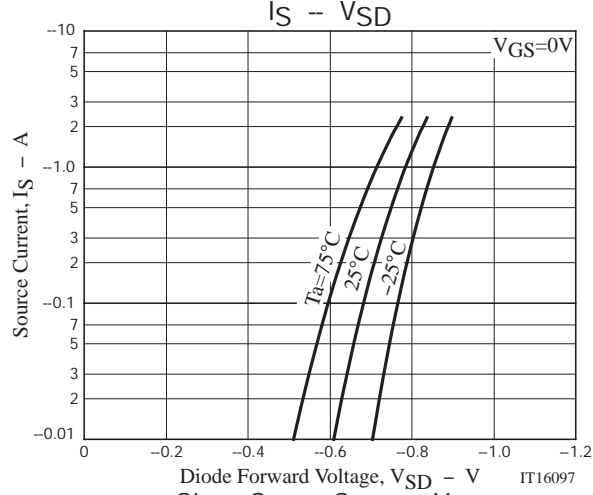
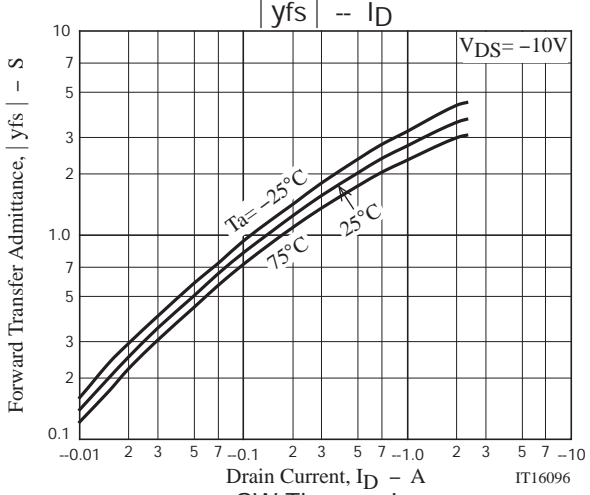
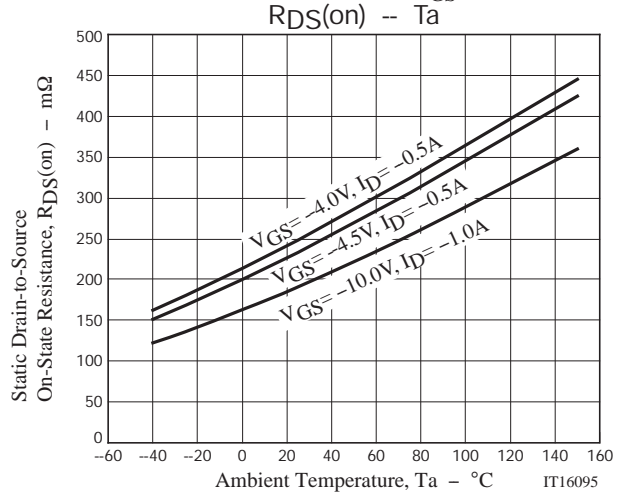
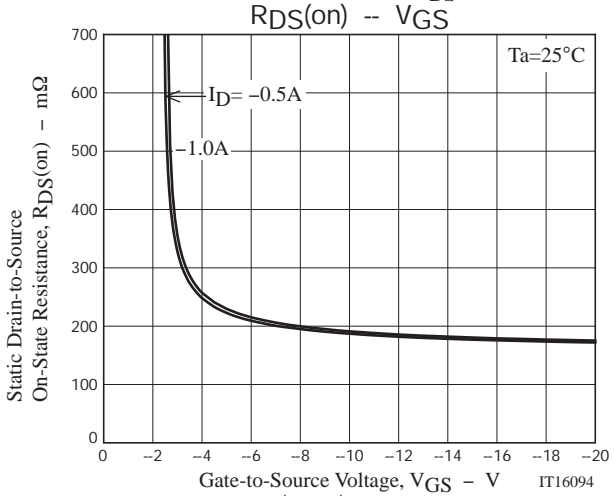
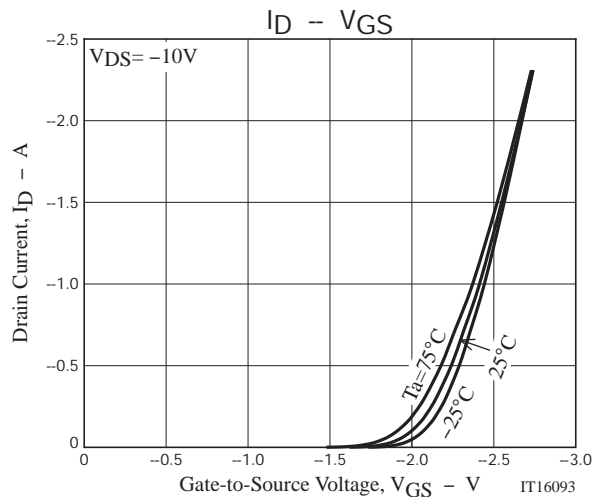
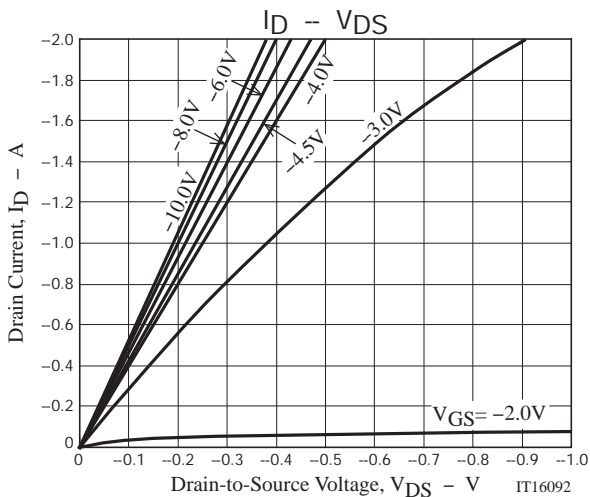
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V(BR)DSS	I _D =-1mA, V _{GS} =0V	-60			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =-60V, V _{GS} =0V			-1	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±16V, V _{DS} =0V			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} =-10V, I _D =-1mA	-1.2		-2.6	V
Forward Transfer Admittance	y _{fs}	V _{DS} =-10V, I _D =-1A		2.7		S
Static Drain-to-Source On-State Resistance	R _{DS(on)1}	I _D =-1A, V _{GS} =-10V		190	250	mΩ
	R _{DS(on)2}	I _D =-0.5A, V _{GS} =-4.5V		235	330	mΩ
	R _{DS(on)3}	I _D =-0.5A, V _{GS} =-4V		250	350	mΩ
Input Capacitance	C _{iss}	V _{DS} =-20V, f=1MHz		262		pF
Output Capacitance	C _{oss}	V _{DS} =-20V, f=1MHz		29		pF
Reverse Transfer Capacitance	C _{rss}	V _{DS} =-20V, f=1MHz		19		pF
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit.		5.1		ns
Rise Time	t _r	See specified Test Circuit.		5.4		ns
Turn-OFF Delay Time	t _{d(off)}	See specified Test Circuit.		34		ns
Fall Time	t _f	See specified Test Circuit.		19		ns
Total Gate Charge	Q _g	V _{DS} =-30V, V _{GS} =-10V, I _D =-1.8A		6.0		nC
Gate-to-Source Charge	Q _{gs}	V _{DS} =-30V, V _{GS} =-10V, I _D =-1.8A		0.83		nC
Gate-to-Drain "Miller" Charge	Q _{gd}	V _{DS} =-30V, V _{GS} =-10V, I _D =-1.8A		1.3		nC
Diode Forward Voltage	V _{SD}	I _S =-1.8A, V _{GS} =0V		-0.82	-1.2	V

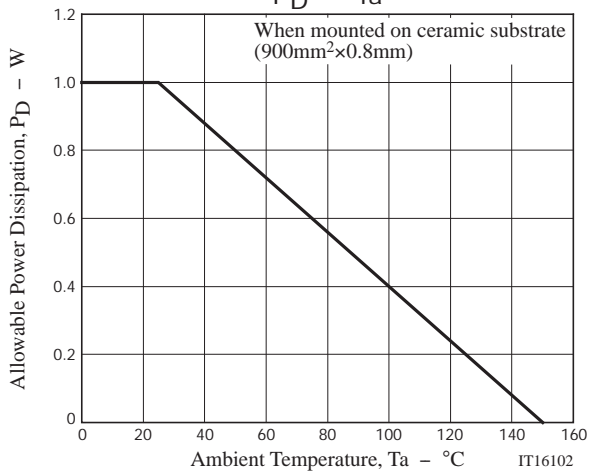
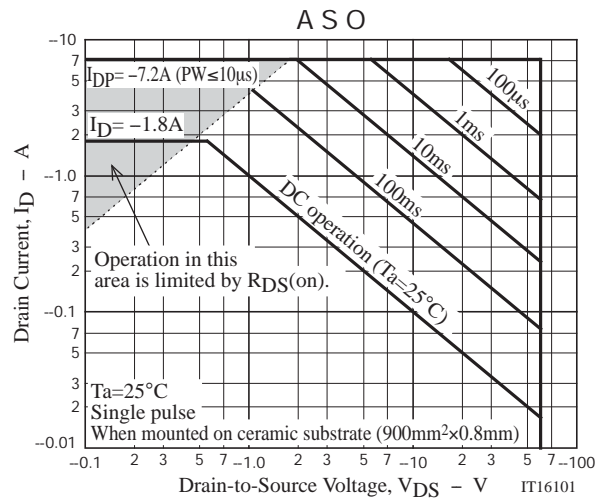
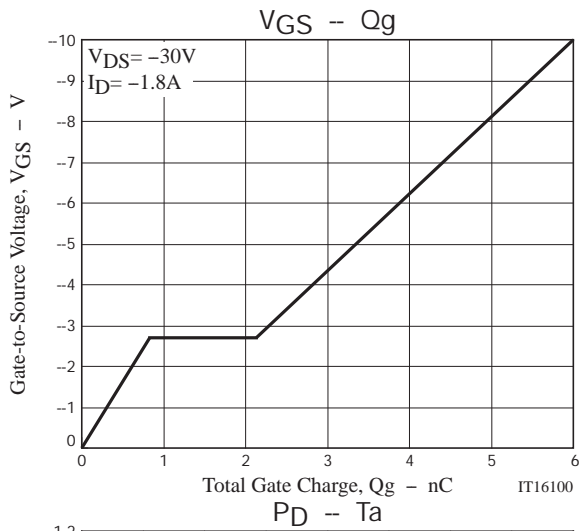
Switching Time Test Circuit



Ordering Information

Device	Package	Shipping	memo
CPH3351-TL-H	CPH3	3,000pcs./reel	Pb Free and Halogen Free



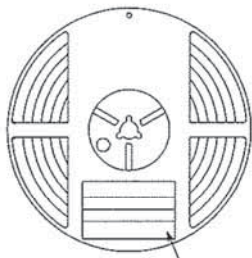


Embossed Taping Specification
CPH3351-TL-H

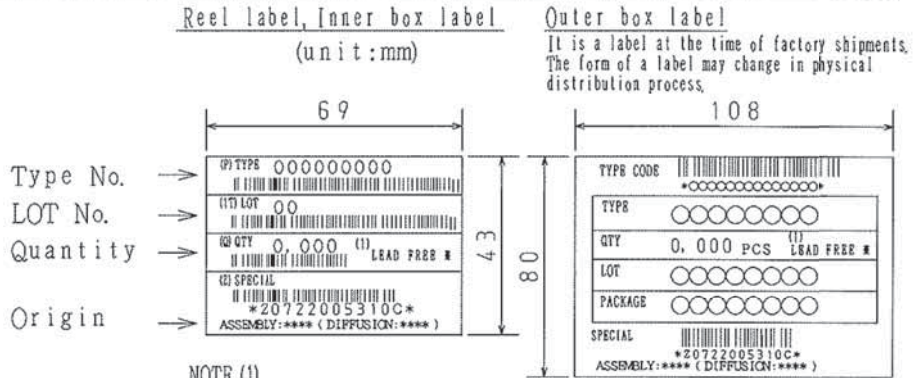
1. Packing Format

Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
CPH3	CPH3	3,000	15,000	90,000	5 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) 440×195×210

Packing method



Reel label



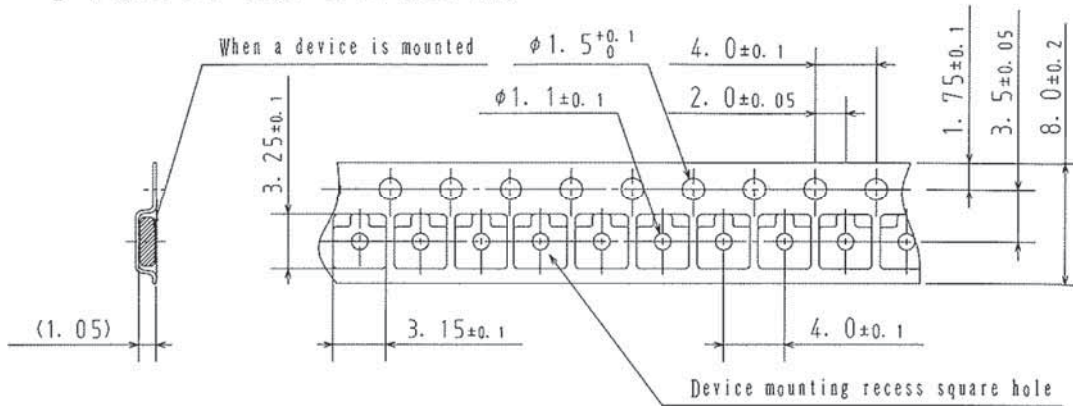
NOTE (1)

The LEAD FREE * description shows that the surface treatment of the terminal is lead free.

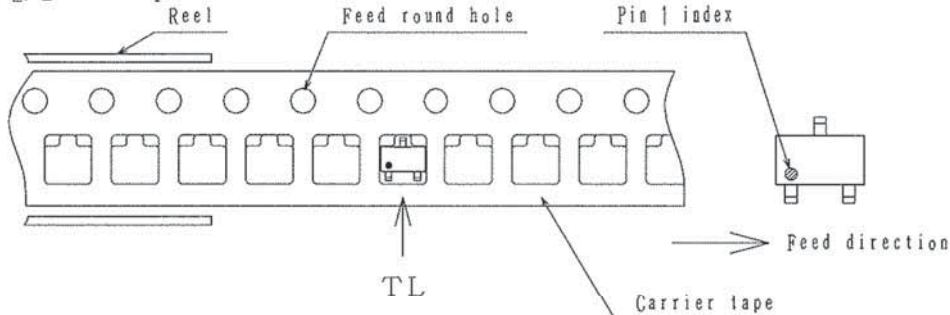
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)



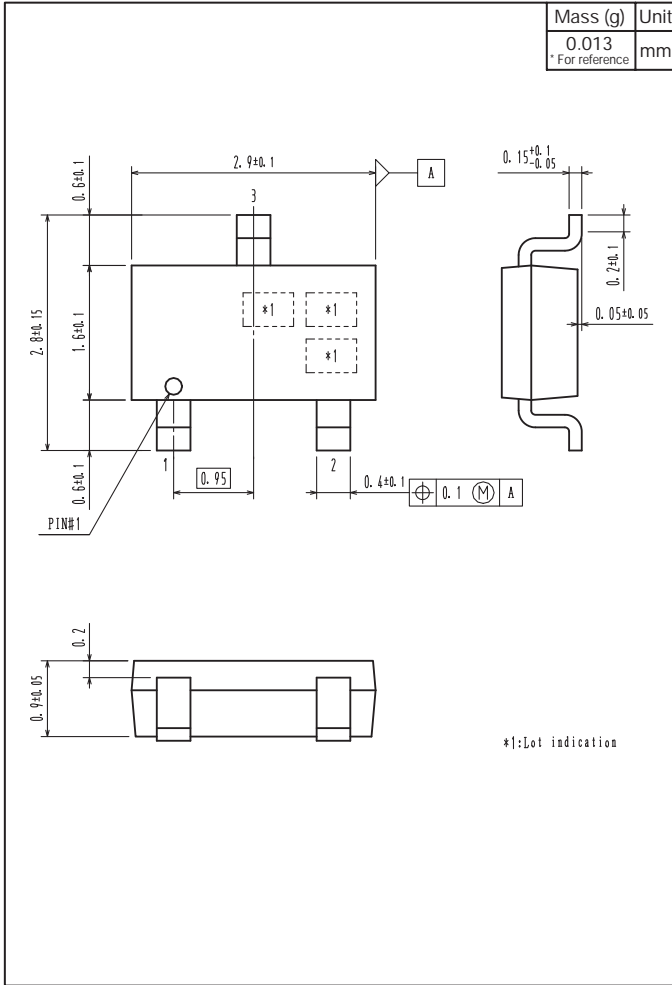
2-2. Device placement direction



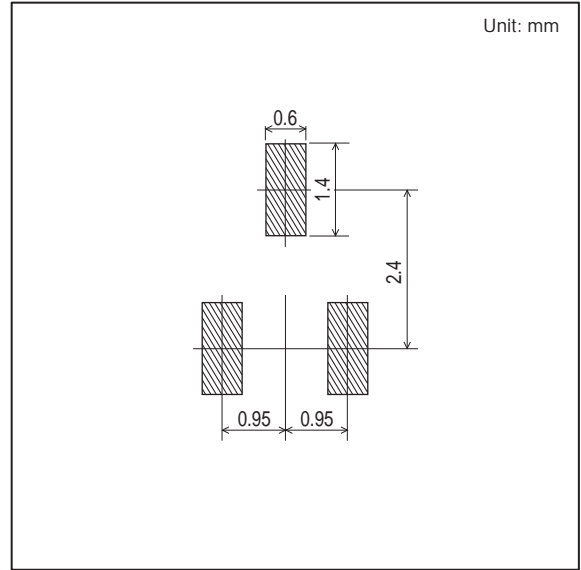
Those with one electrode terminal on the feed hole side.....TL

CPH3351

Outline Drawing CPH3351-TL-H



Land Pattern Example



Note on usage : Since the CPH3351 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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